

Citations for Ion : **In**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1968	Bulthuis, K. 'Anomalous Penetration of Ga and In Implanted in Silicon' <i>Phys. Letters A</i> , 27, 193-94 (1968) <i>Comment</i> : R, dR. 56 keV In, Ga -> Si (Cryst.)	1968-Bult
1971	Gamo, K. Iwaki, M. Masuda, K. Namba, S. Ishihara, S. 'Concentration Profiles of Room Temperature Ion Implanted Indium in Silicon' <i>Jap. J. Appl. Phys.</i> , 10, 523-525 (1971) <i>Comment</i> : R, dR. 20-80 keV In -> Si	1971-Gamo
1971	Gamo, K. Iwaki, M. Masuda, K. Ishihara, S. Kimura, K. 'Concentration Profiles of Ion Implanted Impurities into Silicon' <i>Sci. Pap. Inst. Phys. Chem. Res. (Japan)</i> , 65, 19-21 (1971) <i>Comment</i> : R, dR. 20-80 keV In, 20 keV Sb -> Si	1971-Gamo3
1972	Hart, R. R. Lee, D. H. March, O. J. 'Enhanced Migration of Implanted Sb and In in Si Covered with Evaporated Al' <i>Appl. Phys. Letters</i> , 20, 76-77 (1972) <i>Comment</i> : R. 180 keV Sb, In -> Al, Si	1972-Hart
1973	Gamo, K. Iwaki, M. Masuda, K. Namba, S. Ishihara, S. 'Enhanced Diffusion and Lattice Location of Indium and Gallium Implanted in Silicon' <i>Jap. J. Appl. Phys.</i> , 12, 735-741 (1973) <i>Comment</i> : R. 45 keV In, Ga -> Si	1973-Gamo
1979	Blood, P. Brown, W. L. Miller, G. L. 'Incorporation of Implanted In and Sb in Silicon During Amorphous Layer Regrowth' <i>J. Appl. Phys.</i> , 50, 173-182 (1979) <i>Comment</i> : R, dR. 100, 340 keV In -> Si, 240 keV Sb -> Si	1979-Bloo
1979	Pham, M. T. 'A Very Simple Method for Profiling the Ion-Implanted Si-Surface' <i>Phys. Stat. Sol. A</i> , 49, 261-265 (1979) <i>Comment</i> : R. 30 keV Si, P, B, Ar, As; 12.2 keV In -> Si	1979-Pham
1979	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci.</i> , Ns-26, 1331-1334 (1979) <i>Comment</i> : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si	1979-Sant
1980	Brylowska, I. Subotowicz, M. Paprocki, K. Derewiecki, H. 'Doping Profiles from the Capacity-Voltage (C-V) Characteristics of the [111] Si(P) Single Crystals Doped by the In ⁺ -Ion-Implantation' <i>Rad. Effects</i> , 47, 163-166 (1980) <i>Comment</i> : R, dR. 30-90 keV In -> Si	1980-Bryl

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1986	Geyer, E. Reschke, D. Freitag, K. 'Z1 Stopping Power Oscillation in the Nuclear Stopping Regime as Obtained by Time-of-Flight Spectroscopy of Heavy Ions in Hydrogen' <i>Nucl. Inst. Methods, B15, 81-85 (1986)</i> <i>Comment : S. Heavy Ions (49-65) at 26 - 90 keV -> H2 (gas)</i>	1986-Geye
1986	Izsak, K. Berthold, J. Kalbitzer, S. 'Range Phenomena of Low Energy Ions in Solids' <i>Nucl. Inst. Methods, B15, 34-41 (1986)</i> <i>Comment : R. In, Xe, Pb, Cs, Au, (.01 < epsilon < 1) -> Al, Si, Ni, Ri, Ge, Al2O3</i>	1986-Izsa
1986	Lennard, W. N. Geissel, H. Jackson, D. P. Phillips, D. 'Electronic Stopping Values for Low Velocity Ions (9 <= Z1 <= 92) in Carbon Targets' <i>Nucl. Inst. Methods, B13, 127 (1986)</i> <i>Comment : S. (16 keV/amu) F, Ne, Na, Mg, Al, P, Cl, Ar, K, Sc, Cr, Mn, Cu, Kr, Nb, Ag, In, Xe, Sm, Yb, Au, Bi, U -> C</i>	1986-Lenn2
1987	Freitag, K. Reschke, D. Geyer, E. 'Stopping Power Measurements for Low Energy Ions in Gases by Time-of-Flight Spectroscopy' <i>Nucl. Inst. Methods, B27, 344-352 (1987)</i> <i>Comment : S. Heavy Ions (49-65) at 27 - 90 keV -> H2 (gas)</i>	1987-Frei